UNISONIC TECHNOLOGIES CO., LTD

UT3414 Power MOSFET

N-CHANNEL ENHANCEMENT MODE

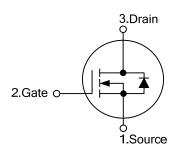
■ DESCRIPTION

The **UT3414** uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications.

■ FEATURES

- * $R_{DS(ON)}$ < $50m\Omega$ @ V_{GS} = 4.5V
- * $R_{DS(ON)}$ < $63m\Omega$ @ V_{GS} = 2.5V
- * $R_{DS(ON)}$ < $87m\Omega$ @ V_{GS} = 1.8V
- * Low capacitance
- * Low gate charge
- * Fast switching capability
- * Avalanche energy specified

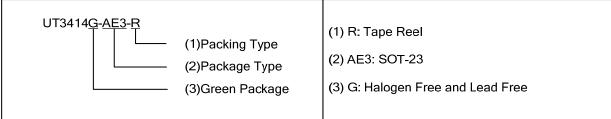
■ SYMBOL



ORDERING INFORMATION

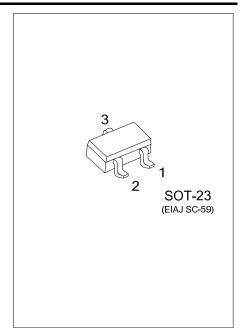
Ordering Number	Package	Pin Assignment			Dooking	
		1	2	3	Packing	
UT3414G-AE3-R	SOT-23	S	G	D	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



■ MARKING





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■ **ABSOLUTE MAXIMUM RATINGS** (T_A = 25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	20	V
Gate-Source Voltage	V_{GSS}	±8	V
Continuous Drain Current	I _D	4.2	Α
Pulsed Drain Current	I _{DM}	15	Α
Power Dissipation	P_D	1.4	W
Junction Temperature	T_J	+150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

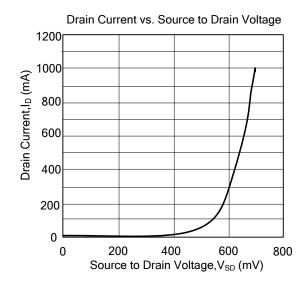
PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction to Ambient	θ_{JA}		100	125	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

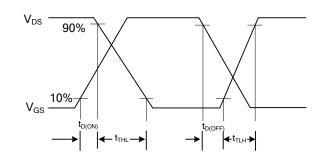
				1		
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA				V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =16V, V _{GS} =0V			1	μΑ
Gate-Source Leakage Current	I_{GSS}	V _{DS} =0V, V _{GS} =±8V			100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu A$	0.4	0.6	1	V
On State Drain Current	I _{D(ON)}	V _{DS} =5V, V _{GS} =4.5V	15			Α
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =4.2A		41	50	mΩ
		V_{GS} =2.5V, I_{D} =3.7A		52	63	
		V _{GS} =1.8V, I _D =3.2A		67	87	
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}			436		pF
Output Capacitance	Coss	V _{DS} =10V, V _{GS} =0V, f=1.0MHz		66		pF
Reverse Transfer Capacitance	C _{RSS}			44		pF
SWITCHING PARAMETERS						
Turn ON Delay Time	t _{D(ON)}			5.5		ns
Turn ON Rise Time	t _R	V_{DS} =10V, V_{GS} =5V, R_L =2.7 Ω		6.3		ns
Turn OFF Delay Time	t _{D(OFF)}	$R_G=6\Omega$		40		ns
Turn OFF Fall-Time	t _F			12.7		ns
Total Gate Charge	Q_{G}			6.2		nC
Gate Source Charge	Q_{GS}	V_{DS} =10V, I_{D} =4.2A, V_{GS} =4.5V		1.6		nC
Gate Drain Charge	Q_{GD}			0.5		nC
SOURCE- DRAIN DIODE RATINGS A	ND CHARAC	CTERISTICS				
Diode Forward Voltage	V_{SD}	V _{GS} =0V, I _S =1A		0.76	1	V
Maximum Body-Diode Continuous					2	Α
Current	I _S					А
Body Diode Reverse Recovery Time	t _{RR}	I _F =4A, dI/dt=100A/μs		12.3		ns
Body Diode Reverse Recovery Charge	Q_{RR}	I _F =4A, dI/dt=100A/μs		3.5		nC

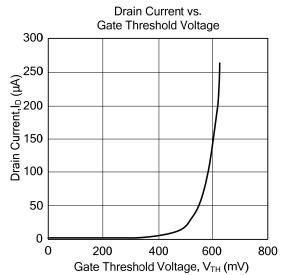
^{2.} Pulse width limited by $T_{J(MAX)}$

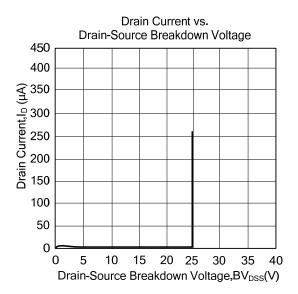
■ TYPICAL CHARACTERISTICS

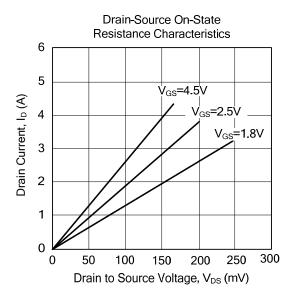


Switching Time Waveforms









UT3414

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